



Aluminum Nitride-Aluminum Oxide Layers For Enhancing The Efficiency Of Group Iii-Nitride Light-Emitting Devices

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Inventors: Zhenqiang Ma, Kwangeun Kim

The Invention

Light-emitting devices having a multiple quantum well (MQW) diode structure and methods of making and using the devices are provided. The devices include aluminum nitride/aluminum oxide bilayers on their hole injection layers. The bilayers improve the energy efficiency of the devices, with respect to devices that lack the bilayers or that include only a layer of aluminum oxide on their hole injection layers.

Additional Information

For More Information About the Inventors

- [Zhenqiang Ma](#)

Tech Fields

- [Semiconductors & Integrated Circuits : Design & fabrication](#)

For current licensing status, please contact Jeanine Burmania at jeanine@warf.org or 608-960-9846